

## Power Modules, Passivated Assembled Circuit Elements, 40 A


**PACE-PAK (D-19)**
**FEATURES**

- Glass passivated junctions for greater reliability
- Electrically isolated base plate
- Available up to 1200  $V_{RRM}/V_{DRM}$
- High dynamic characteristics
- Wide choice of circuit configurations
- Simplified mechanical design and assembly
- UL E78996 approved
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS  
COMPLIANT**
**PRODUCT SUMMARY**

$I_o$	40 A
Type	Modules - Thyristor, Standard
Package	PACE-PAK (D-19)
Circuit	Single phase, hybrid bridge common cathode, Single phase, hybrid bridge doubler connection, Single phase, all SCR bridge

**DESCRIPTION**

The VS-P400 series of integrated power circuits consists of power thyristors and power diodes configured in a single package. With its isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits and battery chargers.

**MAJOR RATINGS AND CHARACTERISTICS**

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_o$	80 °C	40	A
$I_{TSM}$ , $I_{FSM}$	50 Hz	385	A
	60 Hz	400	
$I^2t$	50 Hz	745	A <sup>2</sup> s
	60 Hz	680	
$I^2\sqrt{t}$		7450	A <sup>2</sup> √s
$V_{RRM}$	Range	400 to 1200	V
$V_{ISOL}$		2500	V
$T_J$		-40 to 125	°C
$T_{Stg}$			

**ELECTRICAL SPECIFICATIONS**
**VOLTAGE RATINGS**

TYPE NUMBER	$V_{RRM}/V_{DRM}$ , MAXIMUM REPETITIVE PEAK REVERSE AND PEAK OFF-STATE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	$I_{RRM}$ MAXIMUM AT $T_J$ MAXIMUM mA
VS-P401, VS-P421, VS-P431	400	500	10
VS-P402, VS-P422, VS-P432	600	700	
VS-P403, VS-P423, VS-P433	800	900	
VS-P404, VS-P424, VS-P434	1000	1100	
VS-P405, VS-P425, VS-P435	1200	1300	



ON-STATE CONDUCTION					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum DC output current at case temperature	I <sub>O</sub>	Full bridge circuits		40	A
				80	°C
Maximum peak, one-cycle non-repetitive on-state or forward current	I <sub>TSM</sub> , I <sub>FSM</sub>	t = 10 ms	No voltage reapplied	385	A
		t = 8.3 ms			
		t = 10 ms	100 % V <sub>RRM</sub> reapplied	325	
		t = 8.3 ms			
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	t = 10 ms	No voltage reapplied	745	A <sup>2</sup> s
		t = 8.3 ms			
		t = 10 ms	100 % V <sub>RRM</sub> reapplied	530	
		t = 8.3 ms			
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied I <sup>2</sup> t for time tx = I <sup>2</sup> √t · √tx		7450	A <sup>2</sup> √s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % × π × I <sub>T(AV)</sub> < I < π × I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum		0.83	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	(I > π × I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum		1.03	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % × π × I <sub>T(AV)</sub> < I < π × I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum		9.61	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	(I > π × I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum		7.01	
Maximum on-state voltage drop	V <sub>TM</sub>	I <sub>TM</sub> = π × I <sub>T(AV)</sub>	T <sub>J</sub> = 25 °C	1.4	V
Maximum forward voltage drop	V <sub>FM</sub>	I <sub>FM</sub> = π × I <sub>F(AV)</sub>	T <sub>J</sub> = 25 °C	1.4	V
Maximum non-repetitive rate of rise of turned-on current	di/dt	T <sub>J</sub> = 125 °C from 0.67 V <sub>DRM</sub> I <sub>TM</sub> = π × I <sub>T(AV)</sub> , I <sub>g</sub> = 500 mA, t <sub>r</sub> < 0.5 μs, t <sub>p</sub> > 6 μs		200	A/μs
Maximum holding current	I <sub>H</sub>	T <sub>J</sub> = 25 °C anode supply = 6 V, resistive load		130	mA
Maximum latching current	I <sub>L</sub>			250	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = 125 °C, exponential to 0.67 V <sub>DRM</sub> gate open		200	V/μs
Maximum peak reverse and off-state leakage current at V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>RRM</sub> , I <sub>DRM</sub>	T <sub>J</sub> = 125 °C, gate open circuit		10	mA
Maximum peak reverse leakage current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		100	μA
RMS isolation voltage	V <sub>ISOL</sub>	50 Hz, circuit to base, all terminals shorted, T <sub>J</sub> = 25 °C, t = 1 s		2500	V

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>			8	W
Maximum average gate power	P <sub>G(AV)</sub>			2	
Maximum peak gate current	I <sub>GM</sub>			2	A
Maximum peak negative gate voltage	-V <sub>GM</sub>			10	V
Maximum gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = - 40 °C		3	V
		T <sub>J</sub> = 25 °C		2	
		T <sub>J</sub> = 125 °C		1	
Maximum gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C		90	mA
		T <sub>J</sub> = 25 °C		60	
		T <sub>J</sub> = 125 °C		35	
Maximum gate voltage that will not trigger	V <sub>GD</sub>	T <sub>J</sub> = 125 °C, rated V <sub>DRM</sub> applied		0.2	V
Maximum gate current that will not trigger	I <sub>GD</sub>			2	mA

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range	$T_J, T_{Stg}$		-40 to 125	°C
Maximum thermal resistance, junction to case per junction	$R_{thJC}$	DC operation	1.05	K/W
Maximum thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, smooth and greased	0.10	
Mounting torque, base to heatsink <sup>(1)</sup>			4	Nm
Approximate weight			58	g
			2.0	oz.
Case style			PACE-PAK (D-19)	

**Note**

(1) A mounting compound is recommended and the torque should be checked after a period of 3 hours to allow for the spread of the compound

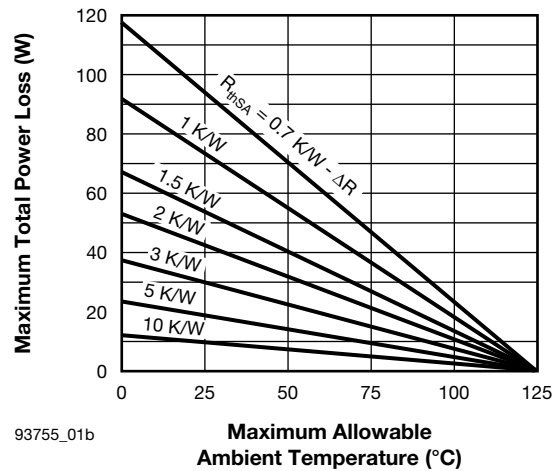


Fig. 1 - Current Ratings Nomogram (1 Module Per Heatsink)



Fig. 2 - On-State Power Loss Characteristics

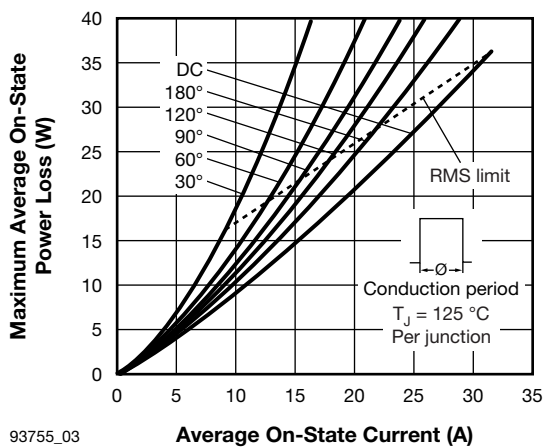


Fig. 3 - On-State Power Loss Characteristics



Fig. 4 - Current Ratings Characteristics

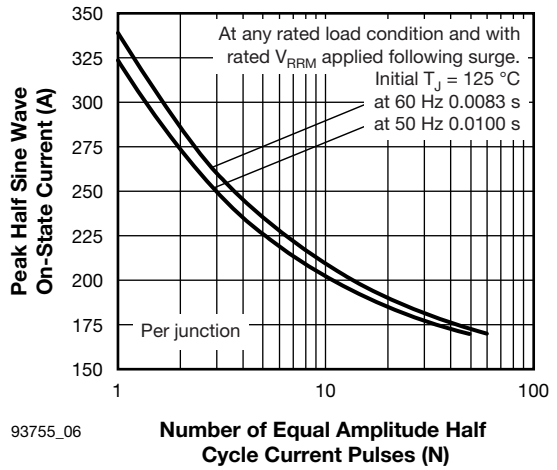


Fig. 6 - Maximum Non-Repetitive Surge Current



Fig. 5 - On-State Voltage Drop Characteristics



Fig. 7 - Maximum Non-Repetitive Surge Current



Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics



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Fig. 9 - Gate Characteristics

**ORDERING INFORMATION TABLE**

Device code	<b>VS-</b>	<b>P</b>	<b>4</b>	<b>0</b>	<b>2</b>	<b>K</b>	<b>W</b>
	(1)	(2)	(3)	(4)	(5)	(6)	(7)

- 1** - Vishay Semiconductors product
- 2** - Module type
- 3** - Current rating  
 1 = 25 A DC (P100 Series)  
 4 = 40 A DC (P400 Series)
- 4** - Circuit configuration  
 0 = Single Phase, Hybrid Bridge Common Cathode  
 2 = Single Phase, Hybrid Bridge Doubler Connection  
 3 = Single Phase, all SCR Bridge
- 5** - Voltage code  
 1 = 400 V  
 2 = 600 V  
 3 = 800 V  
 4 = 1000 V  
 5 = 1200 V
- 6** - K = Optional Voltage Suppression
- 7** - W = Optional Freewheeling Diode

CIRCUIT CONFIGURATION			
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	SCHEMATIC DIAGRAM	TERMINAL POSITIONS
Single phase, hybrid bridge common cathode	0		
Single phase, hybrid bridge doubler connection	2		
Single phase, all SCR bridge	3		

CODING (1)					
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	BASIC SERIES	WITH VOLTAGE SUPPRESSION	WITH FREEWHEELING DIODE	WITH BOTH VOLTAGE SUPPRESSION AND FREEWHEELING DIODE
Single phase, hybrid bridge common cathode	0	P40.	P40.K	P40.W	P40.KW
Single phase, hybrid bridge doubler connection	2	P42.	P42.K	-	-
Single phase, all SCR bridge	3	P43.	P43.K	-	-

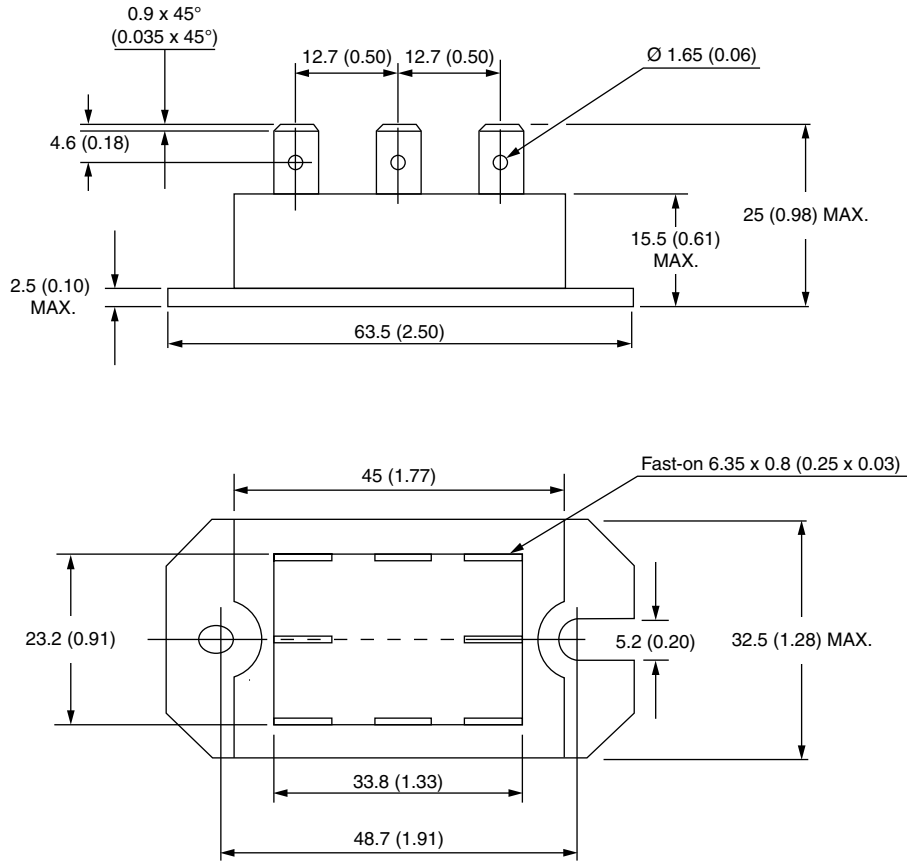
**Note**

(1) To complete code refer to Voltage Ratings table, i.e.: For 600 V P40.W complete code is P402W

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95335">www.vishay.com/doc?95335</a>

## D-19 PACE-PAK

**DIMENSIONS** in millimeters (inches)





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